

1. Material Substrate GaAlAs (N Type) Removed
 Epitaxial Layer GaAlAs (P/N Type)

2. Electrode N(Cathode) Side Gold Alloy
 P(Anode) Side Gold Alloy

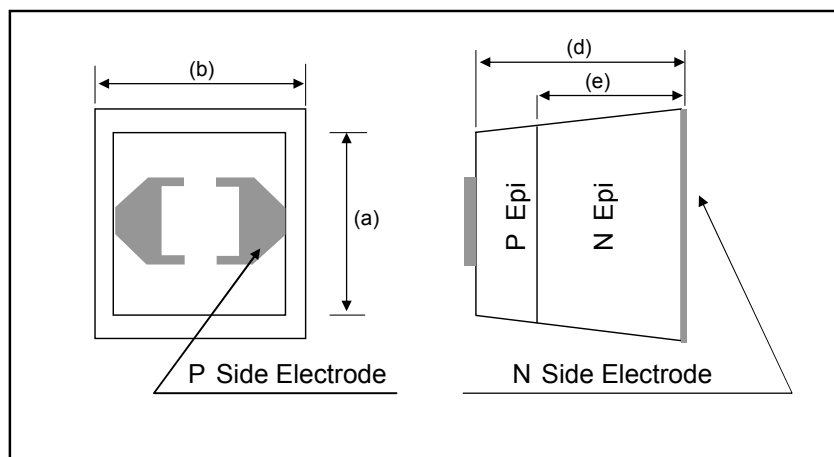
3. Electro-Optical Characteristics

| Parameter | Symbol | Min | Typ | Max | Unit | Condition |
|-----------------|-----------------|-----|-----|-----|------|-----------|
| Forward Voltage | $V_{F(1)}$ | | 1.1 | | V | IF=10uA |
| | $V_{F(2)}$ | | 1.6 | 1.7 | V | IF=50mA |
| Reverse Voltage | V_R | 5 | | | V | IR=10uA |
| Power | P_O | 13 | | | mW | IF=50mA |
| Wavelength | λ_P | | 850 | | nm | IF=50mA |
| | $\Delta\lambda$ | | 45 | | nm | IF=50mA |
| Rise Time | T_r | | 15 | | ns | |
| Fall Time | T_f | | 8 | | ns | |

※ Note : Power is measured by Sorter E/T system with bare chip.

4. Mechanical Data

- (a) Emission Area ----- 18.7mil x 18.7mil
- (b) Bottom Area ----- 19.7mil x 19.7mil
- (c) Bonding Pad ----- double pad
- (d) Chip Thickness ----- 7mil
- (e) Junction Height ----- 5.7mil



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